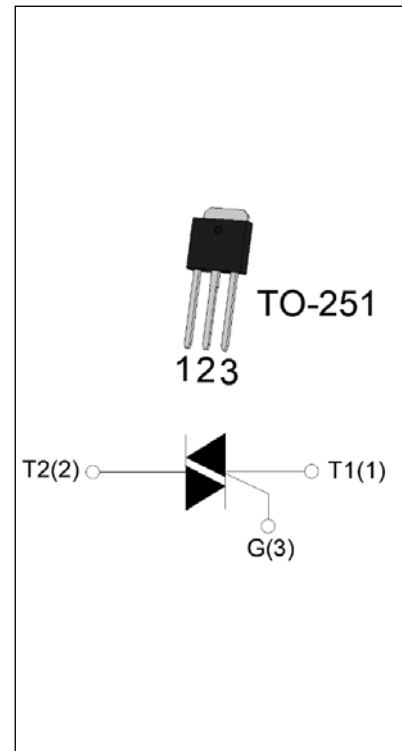


**JST08H-1200CW 8A TRIAC**

Rev.A.1.1

**DESCRIPTION:**

The JST08H-1200CW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST08H-1200CW snubberless triac is especially recommended for use on inductive loads. From T2 terminals to external heatsink. Package TO-251 is RoHS compliant.


**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
$V_{DRM}/V_{RRM}$	1200	V
$I_{GT\ I/II/III}$	35/35/35	mA

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40-150	°C
Operating junction temperature range	$T_j$	-40-125	°C
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	$V_{DRM}$	1200	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )	$V_{RRM}$	1200	V
RMS on-state current ( $T_c \leq 91^\circ\text{C}$ )	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I_{TSM}$	80	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$ , $T_j=25^\circ\text{C}$ )		88	
$I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I^2t$	32	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ , $f=100\text{Hz}$ , $T_j=125^\circ\text{C}$ )	$di/dt$	100	$\text{A}/\mu\text{s}$
Peak gate current ( $t_p=20\mu\text{s}$ , $T_j=125^\circ\text{C}$ )	$I_{GM}$	4	A
Average gate power dissipation ( $T_j=125^\circ\text{C}$ )	$P_{G(AV)}$	0.5	W
Peak gate power	$P_{GM}$	10	W

Peak pulse voltage ( $T_j=25^\circ\text{C}$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	2	kV
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**ELECTRICAL CHARACTERISTICS** ( $T_j=25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12\text{V } R_L=33\Omega$	I - II - III	MAX.	35	mA
$V_{GT}$		I - II - III	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM} T_j=125^\circ\text{C}$ $R_L=3.3\text{k}\Omega$	I - II - III	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	I - III	MAX.	50	mA
		II		60	
$I_H$	$I_T=100\text{mA}$		MAX.	35	mA
dV/dt	$V_D=800\text{V}$ Gate Open $T_j=125^\circ\text{C}$		MIN.	300	V/ $\mu\text{s}$
(dI/dt) <sub>c</sub>	(dV/dt) <sub>c</sub> =20V/ $\mu\text{s}$ , $T_j=125^\circ\text{C}$		MIN.	10	A/ms
$t_{on}$	$I_G=40\text{mA } I_A=200\text{mA } I_R=20\text{mA}$ $T_j=25^\circ\text{C}$		TYP.	3	$\mu\text{s}$
$t_{off}$				30	

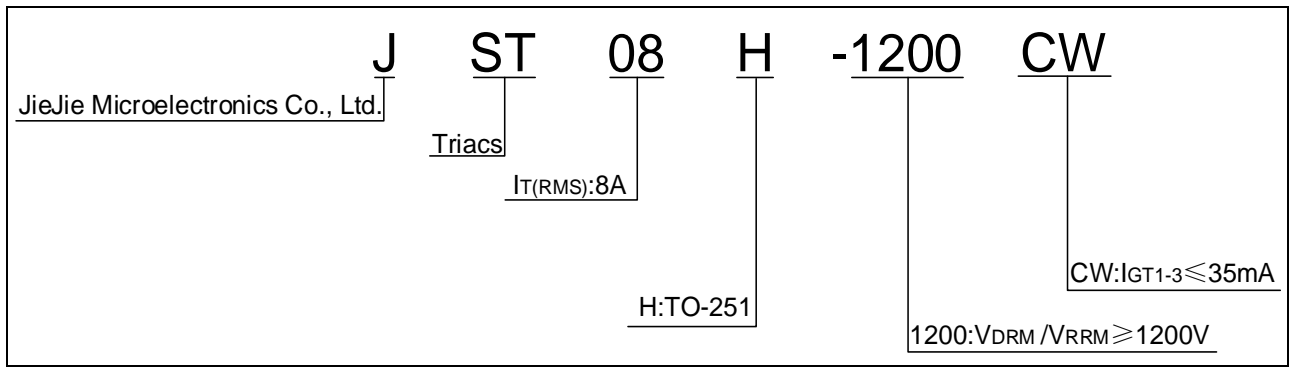
**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=11\text{A } t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5	V
$V_{TO}$	Threshold voltage	$T_j=125^\circ\text{C}$	0.82	V
$R_D$	Dynamic resistance	$T_j=125^\circ\text{C}$	45	m $\Omega$
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	10	$\mu\text{A}$
$I_{RRM}$		$T_j=125^\circ\text{C}$	1	mA

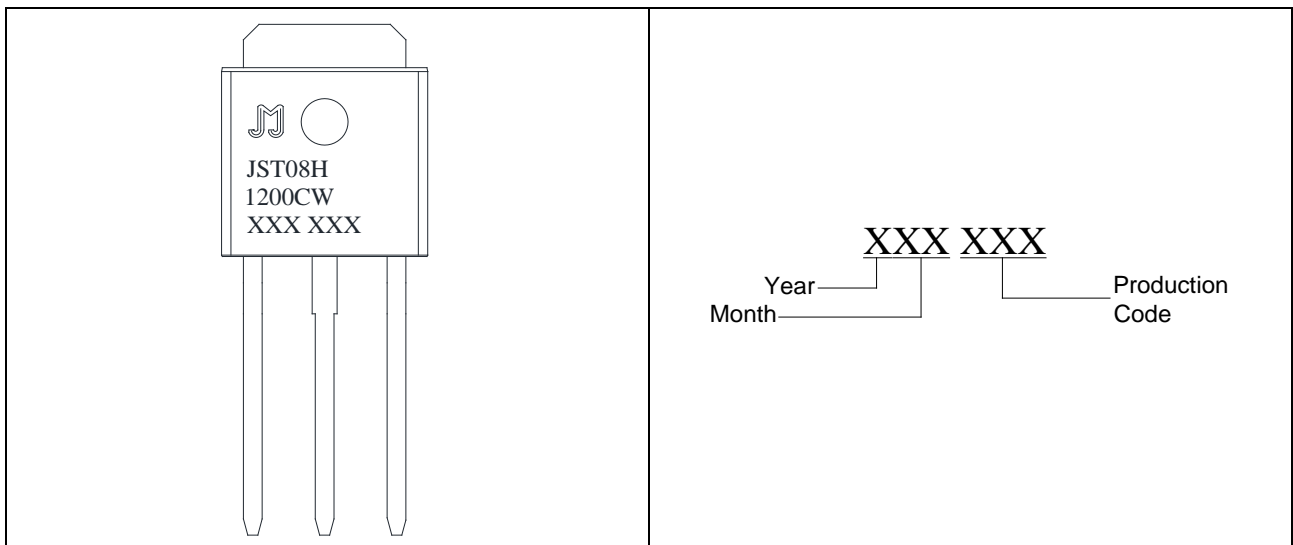
**THERMAL RESISTANCES**

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	3	$^\circ\text{C/W}$
$R_{th(j-a)}$	junction to ambient (AC)	100	$^\circ\text{C/W}$

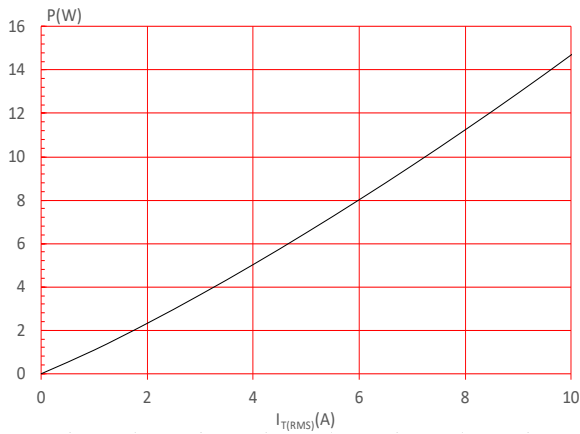
**ORDERING INFORMATION**



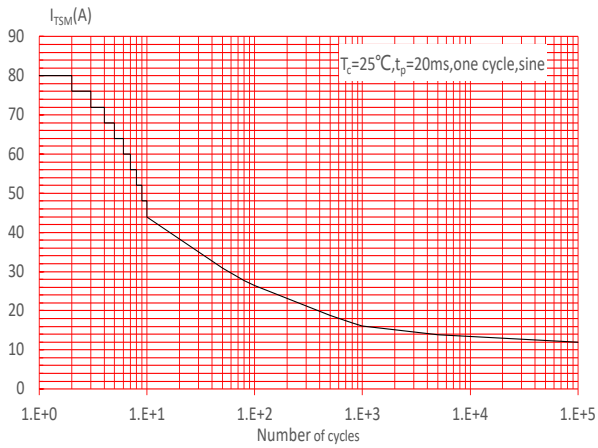
**MARKING**



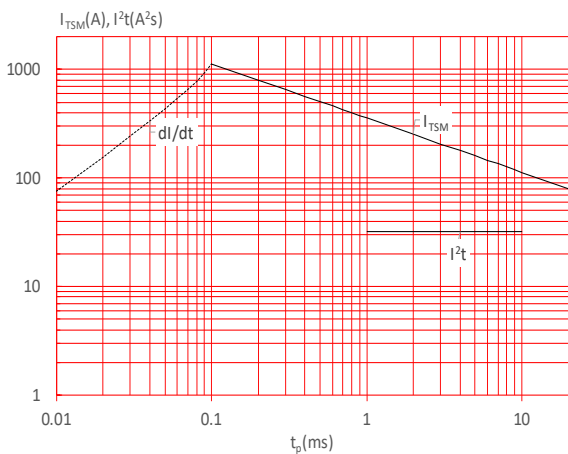
**FIG.1:** Maximum power dissipation versus RMS on-state current



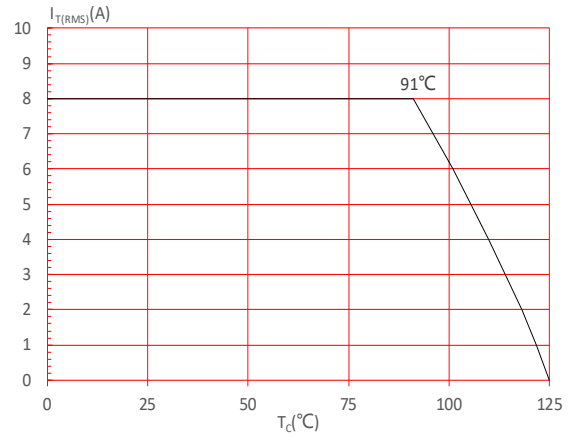
**FIG.3:** Surge peak on-state current versus number of cycles



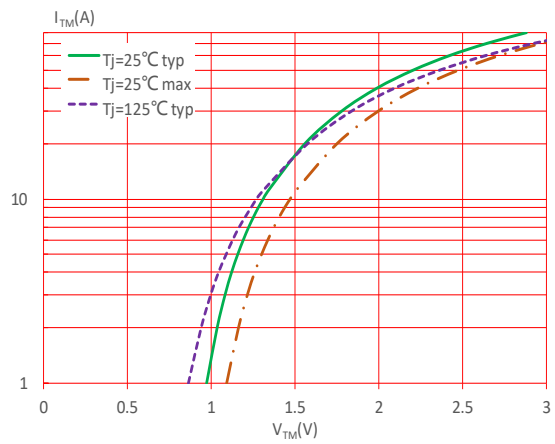
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( $di/dt < 100\text{A}/\mu\text{s}$ )



**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

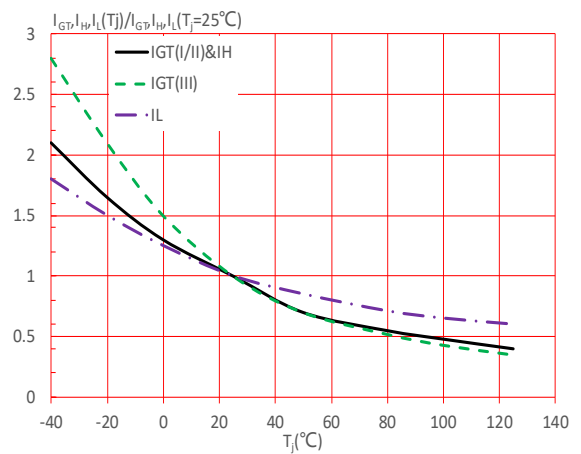
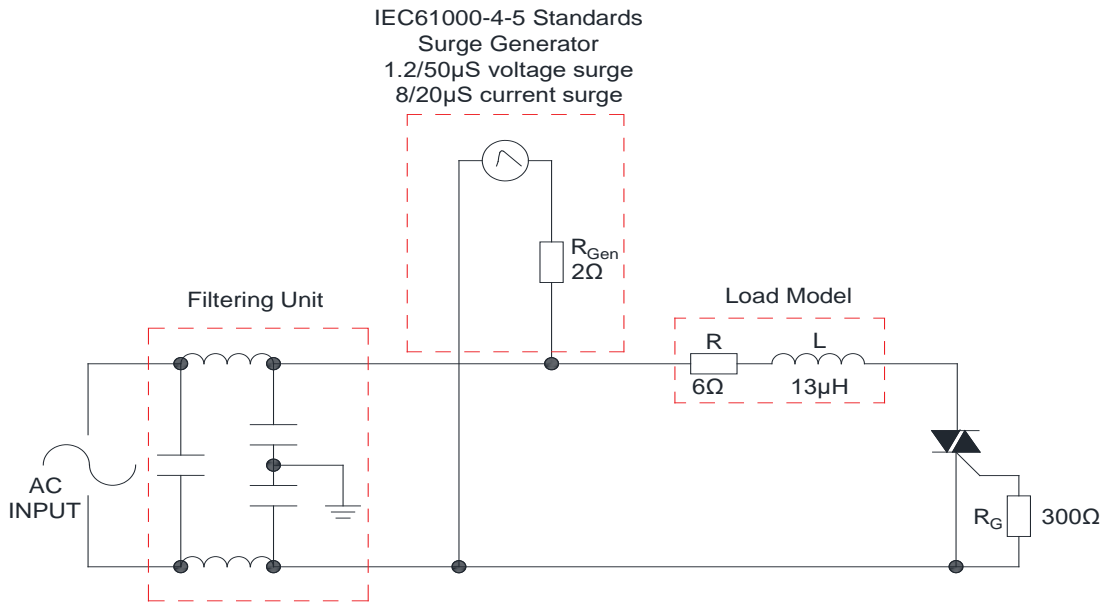


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



## LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics

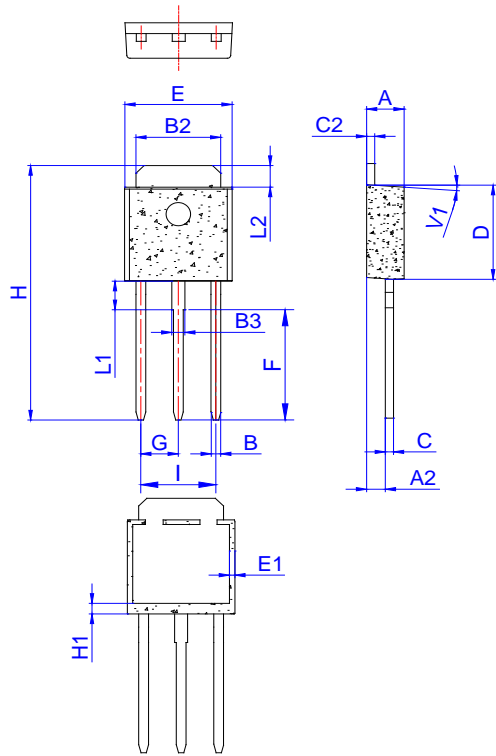
**ORDERING INFORMATION**

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I - II - III			
JST08H-1200CW	1200	35	TO-251	80	Tube

**Document Revision History**

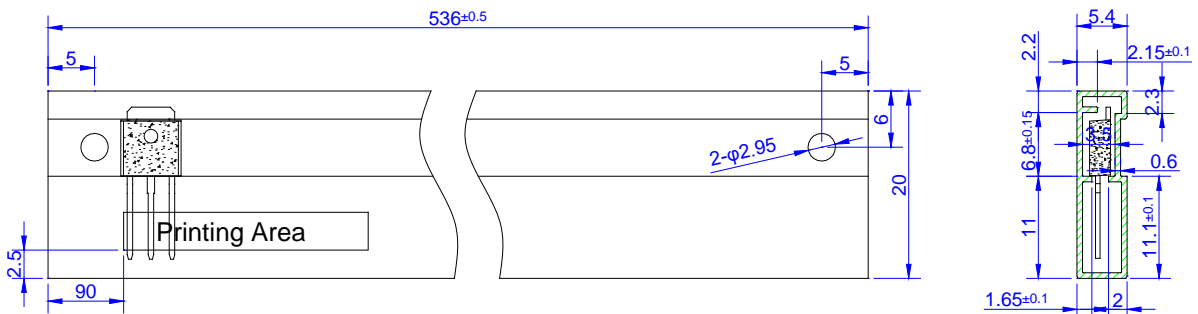
Date	Revision	Changes
Apr.12, 2023	A.1.0	Last updated
Oct.16, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	1.00		1.30	0.039		0.051
B	0.50		0.70	0.020		0.028
B2	5.10		5.40	0.200		0.213
B3	0.70		1.00	0.028		0.039
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
E1	0.60		1.00	0.024		0.039
F	6.90		7.30	0.272		0.287
G	2.20		2.40	0.087		0.094
H	16.00		17.00	0.630		0.669
H1	1.45		1.85	0.057		0.073
I	4.40		4.80	0.173		0.189
L1	1.80		2.20	0.071		0.087
L2	1.25		1.55	0.049		0.061
V1		4°			4°	

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-251	TUBE	80	4,000	20,000

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